

$4M \times 8/2M \times 16~3V$ dual bank flash memory

GENERAL DESCRIPTION

The W19B32XMT/B is a 32Mbit, 2.7~3.6 volt dual bank CMOS flash memory organized as $4M \times 8$ or $2M \times 16$ bits. The word-wide (× 16) data appears on DQ15-DQ0, and byte-wide (× 8) data appears on DQ7–DQ0. The device can be programmed and erased in-system with a standard 2.7~3.6V power supply. A 12-volt VPP is not required. The unique cell architecture of the W19B32XMT/B results in fast program/erase operations with extremely low current consumption (compared to other comparable 3-volt flash memory products). The device can also be programmed and erased by using standard EPROM programmers.

FEATURES

Performance

- 2.7~3.6-volt write (program and erase) operations
- Fast write operation
- Read access time: 70, 90 nS
- Typical program/erase cycles:
 100K
- Twenty-year data retention
- Ultra low power consumption

Architecture

- Dual Bank architectures
 - W19B322M: bank1: 4M; bank2: 28M
 - W19B323M: bank1: 8M; bank2: 24M
 - W19B324M: bank1: 16M; bank2: 16M
- Security Sector Size: 256 Bytes
 - The Security Sector is an OTP; once the sector is programmed, it cannot be erased
- Simultaneous Read/write operation
 - Data can be continuously read from one bank while processing erase/program functions in other bank with zero latency
- JEDEC standard byte-wide and wordwide pinouts
- TTL compatible I/O
- Manufactured on WinStack 0.18μm process technology
- Available packages: 48-pin TSOP and 48-ball TFBGA (8x11mm)

Software Features

 Compatible with common Flash Memory Interface (CFI) specification

- Flash device parameters stored directly on the device
- Allows software driver to identify and use a variety of different current and future Flash products
- Erase Suspend/Erase Resume
 - Suspends erase operations to allow programming in same bank
- End of program detection
 - Software method: Toggle bit/Data polling
- Unlock Bypass Program command
 - Reduces overall programming time when issuing multiple program command sequences

Hardware Features

- Ready/#Busy output (RY/#BY)
- Detect program or erase cycle completion
- Hardware reset pin (#RESET)
 - Reset the internal state machine to the read mode
- #WP/ACC input pin
 - Write protect (#WP) function allows protection of two outermost boot sectors, regardless of sector protection status
 - Acceleration (ACC) function accelerates program timing
- Sector Protection
 - Sectors can be locked in-system or via programmer
 - Temporary Sector Unprotect allows changing data in protected sectors insystem



$4M\times8/2M\times16$ 3V DUAL BANK FLASH MEMORY



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